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Discrete Semiconductors

FET's For VHF Amplifiers and Mixers

Type No.	Case	Pol	IGSS max. nA	Vp max. V	Ciss max. pF	Crss max. pF	Yfs min. μmho	Gps min. dB MHz	NF max. dB MHz
2N3823	TO72	N	0.5	8	6	2	3200	200	2.5 100
2N4416	TO72	N	0.1	6	4	0.8	4000	400	10 400
2N4416A	TO72	N	0.1	6	4	0.8	4000	10	400 400
2N5549	TO18	N	0.25	6	8	2	6000		

For Low Noise Amplifiers

Type No.	Case	Pol	BVDGO min. V	IGSS max. nA	IDSS min. mA	Yfs min. μmho	Vp max. V	Ciss max. pF	Crss max. pF	en @ 10Hz max. nV/ Hz
BFW54	TO72	N	50	0.1	2	3000	6	6	3	100
BFW55	TO72	N	50	0.1	2	3000	6	6	3	40
BFW56	TO72	N	50	0.1	2	3000	6	6	3	20

Dual Gate Mosfets (N Channel Depletion)

Type No.	BV DS V	VP max. V	Yfs min.-max. mmho	Crss max. pF	GPS min. dB @ MHz	N.F. max. dB @ MHz	Notes
3N201	25	5	8-20	0.03	15 200	4.5 200	R.F. Amplifier Mixer I.F. Amplifier } for VHF
3N202	25	5	8-20	0.03	15 200	—	
3N203	25	5	7-15	0.03	20 45	6 45	
3N203A	25	5	7-15	0.03	15 200	4.5 200	
3N204	25	4	10-22	0.03	14 450	5 450	R.F. Amplifier Mixer I.F. Amplifier } for VHF
3N205	25	4	10-22	0.03	17 200	—	
3N206	25	4	7-17	0.03	25 45	4 45	
3N211	27	5.5	17-40	0.05	24 200	3.5 200	R.F. Amplifier Mixer I.F. Amplifier } for VHF/ UHF
3N212	27	4	17-40	0.05	21 200	—	
3N213	35	5.5	15-35	0.05	27 45	4 45	
3N225	20	4	6-15	0.03	10 900	7 900	I.F. Amplifier/ Mixer R.F. Amplifier } for UHF
3N225A	20	3	7.5-15	0.03	14 900	5.5 900	

Case Outline TO72.

Low Leakage/Noise Current

Type No.	Case	Pol.	IGS max. pA	in typ. nV.Hz ^{-1/2}	Yfs min. mS	IDSS min. mA	CISS max. pF	en-100kHz max. nV.Hz ^{-1/2}
BF800	TO-72	N	0.5	3 x 10 ⁻¹⁶	0.25	0.3	—	—
BF801	TO-72	N	1.0	4 x 10 ⁻¹⁶	0.25	0.3	—	—
BF802	TO-72	N	5.0	8 x 10 ⁻¹⁶	0.25	0.3	—	—
BF803	TO-72	N	0.5	3 x 10 ⁻¹⁶	0.25	0.3	1.8	12.0
BF804	TO-72	N	0.5	3 x 10 ⁻¹⁶	0.25	0.3	1.8	12.0
BF805	TO-72	N	2.0	6 x 10 ⁻¹⁶	3.0	3.0	3.5	2.4
BF806	TO-72	N	5.0	10 ⁻¹⁵	3.0	3.0	3.5	2.8

Low Leakage

Type No.	Case	Pol	BVGSS min. V	IGSS max. pA	IDSS min. μA	Yfs min. μS	Vp max. V	CISS max. pF
E8517	TO-72	N	40	10	30	70	1.8	2.0
E8517A	TO-72	N	40	1.0	30	70	1.8	2.0
E8518	TO-72	N	40	10	80	80	3.0	2.0
E8518A	TO-72	N	40	1.0	80	80	3.0	2.0
E8519	TO-72	N	40	10	200	100	6.0	2.0
E8519A	TO-72	N	40	1.0	200	100	6.0	2.0